



Product data sheet

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SOT - 23



2. EMITTER

3. COLLECTOR

MMBTA06 TRANSISTOR (NPN)

FEATURES

- For Switching and Amplifier Applications
- Complementary Type PNP Transistor MMBTA56

MARKING: 1GM

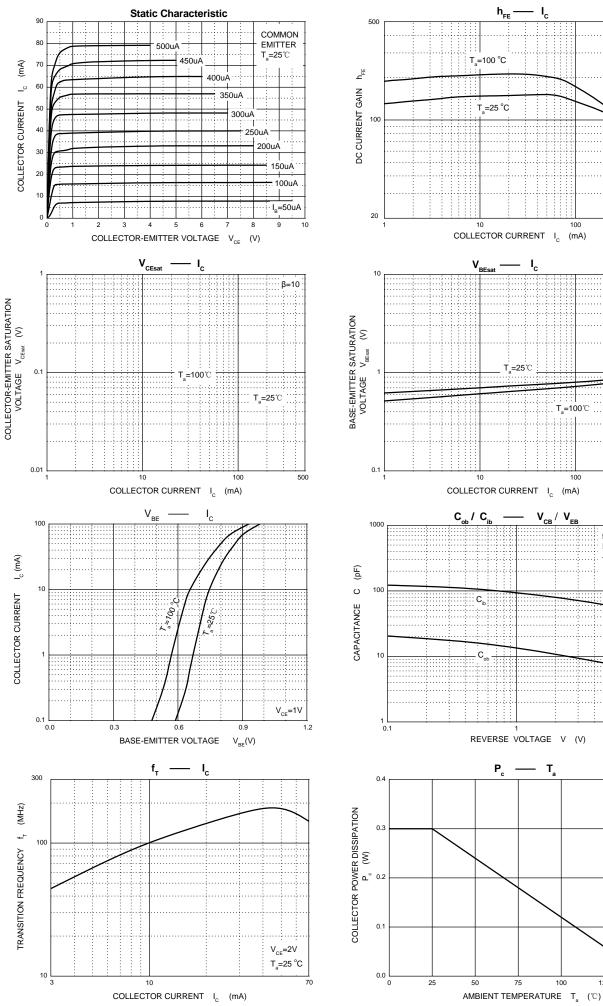
| Symbol | Parameter | Value | Unit |
|----------------------------------|---|----------|------|
| V _{сво} | Collector-Base Voltage | 80 | V |
| VCEO | Collector-Emitter Voltage | 80 | V |
| V _{EBO} | Emitter-Base Voltage | 4 | V |
| lc | Collector Current | 500 | mA |
| Pc | Collector Power Dissipation | 300 | mW |
| R _{oja} | Thermal Resistance From Junction To Ambient | 416 | °C/W |
| T _J ,T _{stg} | Operation Junction and Storage Temperature Range | -55~+150 | °C |

MAYIMUM DATINGS (T

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Тур | Max | Unit |
|--------------------------------------|----------------------|--|-----|-----|------|------|
| Collector-base breakdown voltage | V _{(BR)CBO} | I _C =0.1mA, I _E =0 | 80 | | | V |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | I _C =1mA, I _B =0 | 80 | | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E =0.1mA, I _C =0 | 4 | | | V |
| Collector cut-off current | I _{СВО} | V _{CB} =80V, I _E =0 | | | 0.1 | μA |
| Collector cut-off current | I _{CEO} | V _{CE} =60V, I _B =0 | | | 1 | μA |
| Emitter cut-off current | I _{EBO} | V _{EB} =3V, I _C =0 | | | 0.1 | μA |
| DC current gain | $h_{FE(1)}$ | V _{CE} =1V, I _C =10mA | 100 | | 400 | |
| | h _{FE(2)} | V _{CE} =1V, I _C =100mA | 100 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _C =100mA, I _B =10mA | | | 0.25 | V |
| Base-emitter saturation voltage | V _{BE(sat)} | I _C =100mA, I _B =10mA | | | 1.2 | V |
| Transition frequency | f⊤ | V _{CE} =2V,I _C =10mA, f=100MHz | 100 | | | MHz |



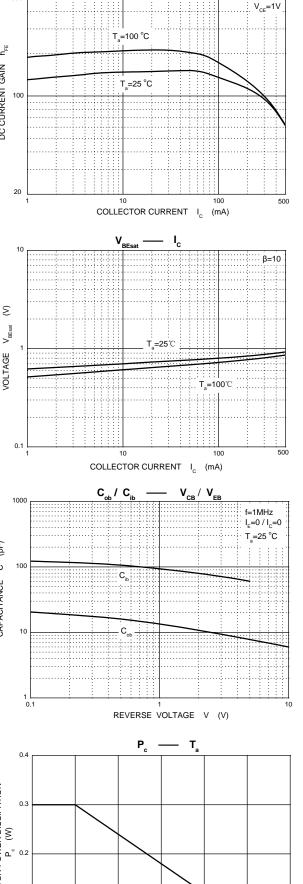




Semiconductor

h_{FE}

– I_c



150

100

50

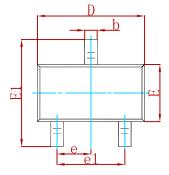
75

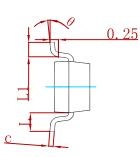
125

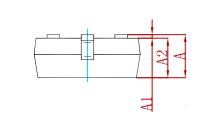




PACKAGE MECHANICAL DATA

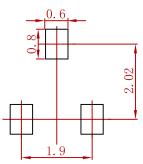






| Symbol | Dimensions In Millimeters | | Dimensions In Inches | | |
|--------|---------------------------|-------|----------------------|-------|--|
| Symbol | Min | Max | Min | Max | |
| Α | 0.900 | 1.150 | 0.035 | 0.045 | |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 | |
| b | 0.300 | 0.500 | 0.012 | 0.020 | |
| с | 0.080 | 0.150 | 0.003 | 0.006 | |
| D | 2.800 | 3.000 | 0.110 | 0.118 | |
| E | 1.200 | 1.400 | 0.047 | 0.055 | |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| е | 0.950 TYP | | 0.037 | 7 TYP | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 | |
| L | 0.550 REF | | 0.022 REF | | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 | |
| θ | 0° | 8° | 0° | 8° | |

Suggested Pad Layout



Note:

Controlling dimension:in millimeters.
General tolerance:± 0.05mm.
The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|---------|--------|------|
| MMBTA06 | SOT-23 | 3000 |





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